

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

Claims 1-8 (cancelled)

Claim 9 (original): A method for producing a semiconductor light emitting device, the method comprising the steps of:

growing a nitride semiconductor material on a substrate to form an n-type layer;

forming a multiple quantum well structure active layer including a plurality of well layers each made of $\text{In}_x\text{Ga}_{(1-x-y)}\text{Al}_y\text{N}$ ($0 \leq x$, $0 \leq y$, $x+y < 1$) and a plurality of barrier layers each made of $\text{In}_s\text{Ga}_{(1-s-t)}\text{Al}_t\text{N}$ ($0 \leq s$, $0 \leq t$, $s+t < 1$), the multiple quantum well structure active layer being provided on the n-type layer; and

growing a nitride semiconductor material on the multiple quantum well structure active layer to form a p-type layer,

wherein the step of growing the p-type layer includes the step of growing a nitride semiconductor material in an atmosphere not containing hydrogen gas while keeping a temperature of the substrate at a first growth temperature.

Claim 10 (original): A method according to claim 9, wherein the step of forming the p-type layer further includes the step of lowering the temperature of the substrate from the first growth temperature to about 400°C in the atmosphere not containing hydrogen gas after the step of growing the nitride semiconductor material in the atmosphere not containing hydrogen gas.